NSN 5961-01-334-8648

Unitized Semiconductor Devices - Page 1 of 1

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Inclosure Material:

Ceramic

Overall Length:

Between 0.660 inches and 0.785 inches

Terminal Length:

0.300 inches

Overall Height:

0.200 inches

Overall Width:

Between 0.220 inches and 0.280 inches

Component Name And Quantity:

4 transistor

Mounting Method:

Terminal

Features Provided:

Electrostatic sensitive

Semiconductor Material:

Silicon all transistor

Voltage Rating In Volts Per Characteristic:

30.0 collector to emitter voltage/static/base open all transistor and 60.0 collector to base voltage/static/emitter open all transistor and 5.0 emitter to base voltage, static, collector open all transistor

Current Rating Per Characteristic:

300.00 milliamperes source cutoff current all transistor

Power Rating Per Characteristic:

1.9 watts small-signal input power, common-collector absolute all transistor

Maximum Operating Tempurature Per Measurement Point:

200.0 degrees celsius junction

Special Features:

All transistor junction pattern arrangement: npn

Terminal Type And Quantity:

14 printed circuit

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

No

Fiig:

A110a0